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APPLICATION NO.	FILIN	IG DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/654,226	09/0	02/2003	Ammar Derraa	3882.8US (99-0017.08/US)	4741
24247	7590	06/15/2004		EXAM	INER
TRASK BRITT				SANTIAGO, MARICELI	
P.O. BOX 2:	550			ADTIBUT	PAPER NUMBER
SALT LAKI	E CITY, UT	84110		ART UNIT	PAPER NUMBER
				2879	
				DATE MAILED: 06/15/200/	1

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)			
	10/654,226	DERRAA, AMMAR			
Office Action Summary	Examin r	Art Unit	)		
	Mariceli Santiago	2879	And I		
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence addre	ess		
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period versilure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days will apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE!	nely filed s will be considered timely. the mailing date of this comn D (35 U.S.C. § 133).	nunication.		
Status					
1)⊠ Responsive to communication(s) filed on <u>04 M</u>	arch 2004.				
2a) This action is <b>FINAL</b> . 2b) ☐ This	action is non-final.				
· · · · · · · · · · · · · · · · · · ·	· <u> </u>				
Disposition of Claims					
4) ⊠ Claim(s) 1-18 is/are pending in the application.  4a) Of the above claim(s) is/are withdray  5) □ Claim(s) is/are allowed.  6) ⊠ Claim(s) 1-18 is/are rejected.  7) □ Claim(s) is/are objected to.  8) □ Claim(s) are subject to restriction and/or	wn from consideration.				
Application Papers					
9) ☐ The specification is objected to by the Examine 10) ☑ The drawing(s) filed on 02 September 2003 is/a Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) ☐ The oath or declaration is objected to by the Ex	are: a)⊠ accepted or b)⊡ objec drawing(s) be held in abeyance. See ion is required if the drawing(s) is obj	e 37 CFR 1.85(a). jected to. See 37 CFR	1.121(d).		
Priority under 35 U.S.C. § 119					
<ul> <li>12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).</li> <li>a) All b) Some * c) None of:</li> <li>1. Certified copies of the priority documents have been received.</li> <li>2. Certified copies of the priority documents have been received in Application No</li> <li>3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> </ul>					
Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	ate	52)		

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#### **DETAILED ACTION**

#### Response to Amendment

The Amendment, filed on March 4, 2004, has been entered and acknowledged by the Examiner.

Claims 1-18 are pending in the instant application.

## **Double Patenting**

The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970);and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

Claims 1-18 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 1, 10 and 14 of U.S. Patent No. 6,326,222. Although the conflicting claims are not identical, they are not patentably distinct from each other for the following reasons.

U.S. Application	U.S. Patent	Reasons for rejection under obviousness-type double patenting
SN 10/654,226	No. 6,326,222	
Claim 1	Claim 1	Patent '222 claims a method of fabricating at least one emission
	i :	structure, comprising forming at least one conductive structure
		extending across at least a portion of a substrate, substantially
		removing a longitudinal portion of the at least one conductive
		structure (patterning) to define at least one conductive layer
		substantially perpendicular (parallel rows) to the substrate, the

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		substrate being exposed along a length of the at least one
		conductive layer, and forming at least one emission structure
		adjacent the at lest one conducive layer.
Claim 2	Claim 1	Patent '222 claims a method wherein the at least one emission
		structure includes an emitter tip.
Claim 3	Claim 1	Patent '222 claims a method wherein the at least one emission
		structure includes a corresponding resistor.
Claim 4	Claim 1	Patent '222 claims a method wherein the resistor is adjacent the at
		least one conductive layer.
Claim 5	Claim 1	Patent '222 claims a method wherein the at least one emission
		structure comprises a plurality of lines of emission structures.
Claim 6	Claim 1	Patent '222 claims a method wherein the emission structure located
		along a first line of the plurality of lines is isolated from at least one
		emission structure located an adjacent, second line of the plurality of
		lines.
Claim 7	Claim 1	Patent '222 claims a method wherein the conductive material over
		the substrate is patterned.
Claim 8	Claim 1	Patent '222 claims a method wherein the at least one emission
		structure is formed from at least one of semiconductive or conductive
		materials.
Claim 9	Claim 10	Patent '222 claims a method wherein the at least one emission
		structure extends over a lateral (peripheral) edge of the at least one
		conductive structure.
Claim 10	Claim 1	Patent '222 claims a method for fabricating at least one emission
		structure, comprising forming at least one conductive structure that
		extends at least partially across a substrate, forming at least one
		emitter tip and a corresponding resistor adjacent to the at least one
		conductive structure, and substantially removing (patterning) at least
		a longitudinal portion of the at least one conductive structure along
		substantially an entire length thereof to define at least one
		conductive layer substantially perpendicular (parallel rows) to the
		substrate.
Claim 11	Claim 1	Patent '222 claims a method wherein the conductive material over
		the substrate is patterned.
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Claim 12	Claim 1	Patent '222 claims a method wherein the at least one emission
		structure is formed from at least one of semiconductive or conductive
		materials.
Claim 13	Claim 1	Patent '222 claims a method wherein the at least one
		emission/resistor structure is formed from at least one of
		semiconductive or conductive materials.
Claim 14	Claim 14	Patent '222 claims a method wherein forming the at least one emitter
		tip comprises disposing at least one layer comprising at least one of
		semiconductive material and conductive material over the substrate
		and the at least one conductive structure, removing a longitudinal
		portion of at least one region of the at least one layer located over
		the at least one conductive structure to expose at least a
		substantially longitudinal portion of the at least one conductive
		structure, and patterning at least one remaining portion of the at least
		one layer.
Claim 15	Claim 14	Patent '222 claims a method wherein at least one emitter tip is
		defined.
Claim 16	Claim 14	Patent '222 claims a method including a corresponding resistor.
Claim 17	Claim 10	Patent '222 claims a method wherein the substantially removing
		comprises leaving at least a lateral edge (conductive traces) of the at
		least one conductive structure along substantially the entire length
		thereof
Claim 18	Claim 10	Patent '222 claims a method wherein the at least one emission
		structure extends over a lateral (peripheral) edge of the at least one
		conductive structure.
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### **Contact Information**

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Mariceli Santiago whose telephone number is (571) 272-2464. The examiner can normally be reached on Monday-Friday from 9:30 AM to 6:00 PM.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nimesh Patel, can be reached on (571) 272-2457. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about PAIR system, see <a href="http://pair-direct.uspto.gov">http://pair-direct.uspto.gov</a>. Should you have questions on access to Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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